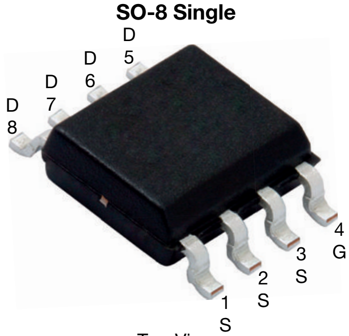
N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω) MAX.	I_D (A) [a]	Q_g (TYP.)
100	0.026 at V_{GS} = 10 V	10.3	5.8 nC
	0.033 at V_{GS} = 4.5 V	9.2	

SO-8 Single



Top View

Ordering Information:
Si4058DY-T1-GE3 (lead (Pb)-free and halogen-free)

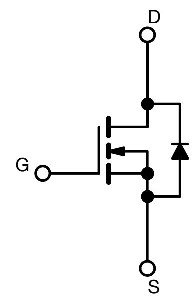
FEATURES

- ThunderFET® power MOSFET
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Pb-free
RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS

- DC/DC primary side switch
- Synchronous rectification
- Fast charger
- Industrial



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	10.3	A
	T_C = 70 °C		8.3	
	T_A = 25 °C		7 [b, c]	
	T_A = 70 °C		5.5 [b, c]	
Pulsed Drain Current (t = 300 μs)		I_{DM}	50	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	5	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	15	
Avalanche Energy		E_{AS}	11.2	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	5.6	W
	T_C = 70 °C		3.6	
	T_A = 25 °C		2.6 [b, c]	
	T_A = 70 °C		1.6 [b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +150	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum Junction-to-Ambient [b, d]	t ≤ 10 s	R_{thJA}	39	48	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	18	22	

Notes
a. Based on T_C = 25 °C.
b. Surface mounted on 1" x 1" FR4 board
c. t = 10 s.
d. Maximum under steady state conditions is 90 °C/W.

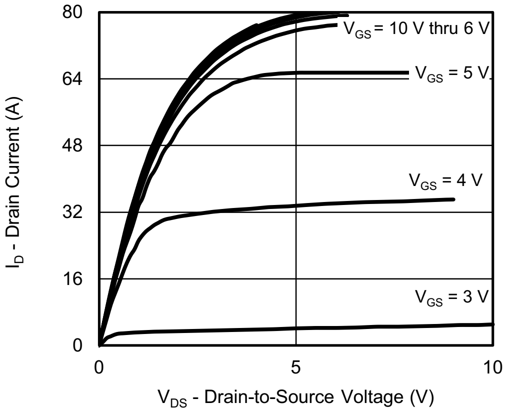
SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 μA	100	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 μA	-	61	-	mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		-	-3.8	-	
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	1.2	-	2.8	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 100 V, V_{GS} = 0 V	-	-	1	μA
		V_{DS} = 100 V, V_{GS} = 0 V, T_J = 70 °C	-	-	10	
On-State Drain Current [a]	$I_{D(on)}$	$V_{DS} \geq$ 5 V, V_{GS} = 10 V	20	-	-	A
Drain-Source On-State Resistance [a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 10 A	-	0.0217	0.0260	Ω
		V_{GS} = 4.5 V, I_D = 8 A	-	0.0266	0.0330	
Forward Transconductance [a]	g_{fs}	V_{DS} = 15 V, I_D = 10 A	-	31	-	S
Dynamic [b]						
Input Capacitance	C_{iss}	V_{DS} = 50 V, V_{GS} = 0 V, f = 1 MHz	-	690	-	pF
Output Capacitance	C_{oss}		-	280	-	
Reverse Transfer Capacitance	C_{rss}		-	11	-	
Total Gate Charge	Q_g	V_{DS} = 50 V, V_{GS} = 10 V, I_D = 10 A	-	12	18	nC
		V_{DS} = 50 V, V_{GS} = 4.5 V, I_D = 10 A	-	5.8	9	
Gate-Source Charge	Q_{gs}		-	2.1	-	
Gate-Drain Charge	Q_{gd}		-	2.2	-	
Output Charge	Q_{oss}	V_{DS} = 50 V, V_{GS} = 0 V	-	22.5	35	
Gate Resistance	R_g	f = 1 MHz	0.8	2.2	4.0	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 50 V, R_L = 5 Ω $I_D \cong$ 10 A, V_{GEN} = 4.5 V, R_g = 1 Ω	-	8	16	ns
Rise Time	t_r		-	17	34	
Turn-Off Delay Time	$t_{d(off)}$		-	11	22	
Fall Time	t_f		-	8	16	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 50 V, R_L = 5 Ω $I_D \cong$ 10 A, V_{GEN} = 10 V, R_g = 1 Ω	-	7	14	
Rise Time	t_r		-	16	32	
Turn-Off Delay Time	$t_{d(off)}$		-	12	24	
Fall Time	t_f		-	7	14	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C	-	-	5	A
Pulse Diode Forward Current [a]	I_{SM}		-	-	50	
Body Diode Voltage	V_{SD}	I_S = 5 A	-	0.81	1.1	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 10 A, di/dt = 100 A/μs, T_J = 25 °C	-	56	112	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	60	120	nC
Reverse Recovery Fall Time	t_a		-	48	-	ns
Reverse Recovery Rise Time	t_b		-	8	-	

Notes

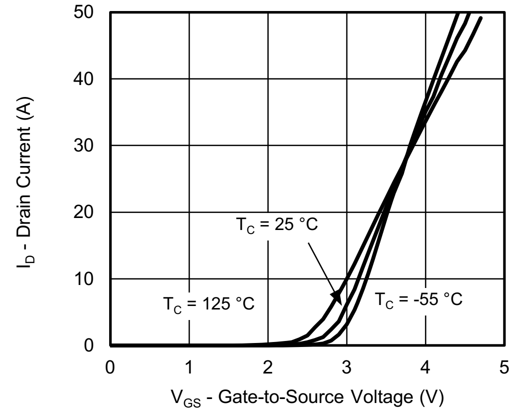
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

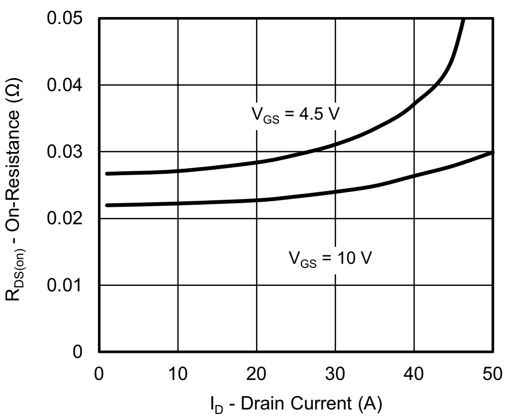
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



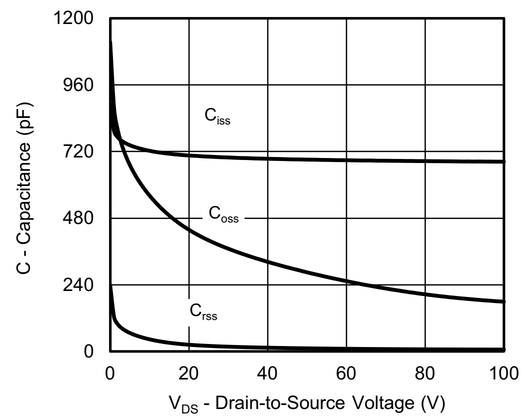
Output Characteristics



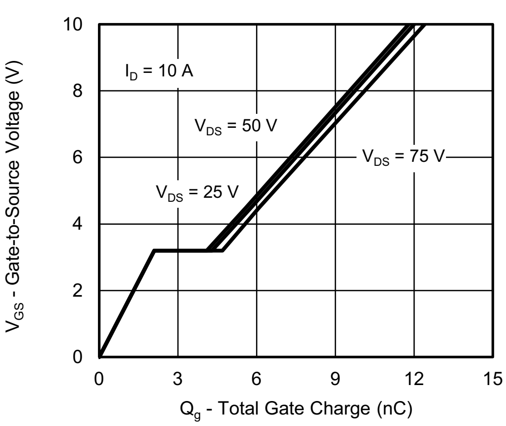
Transfer Characteristics



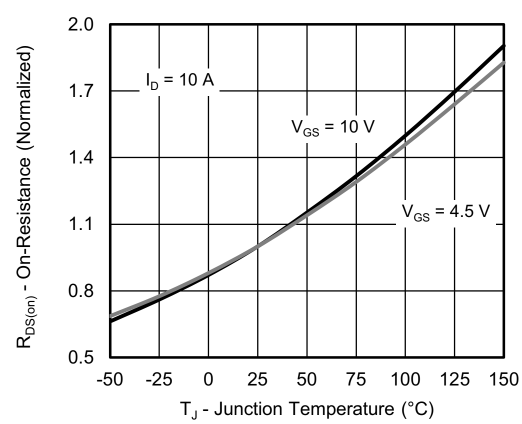
On-Resistance vs. Drain Current



Capacitance

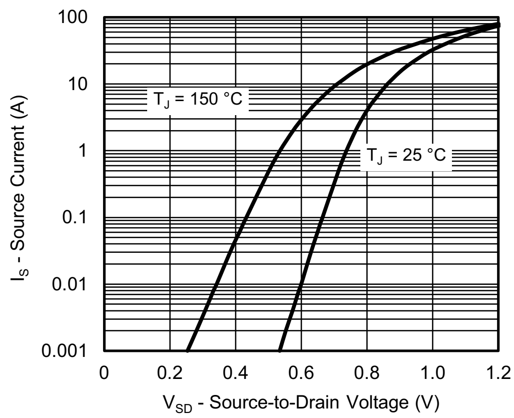


Gate Charge

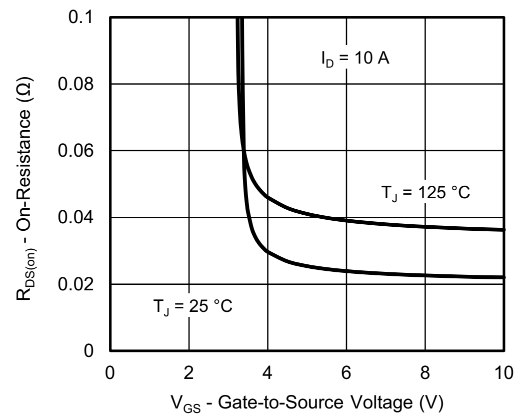


On-Resistance vs. Junction Temperature

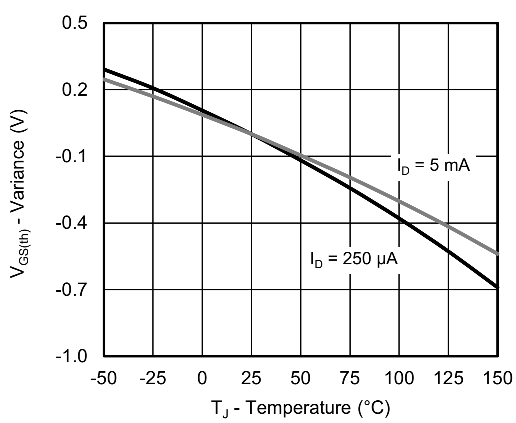
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



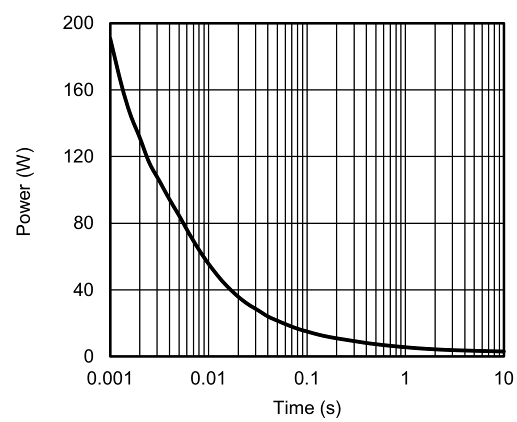
Source-Drain Diode Forward Voltage



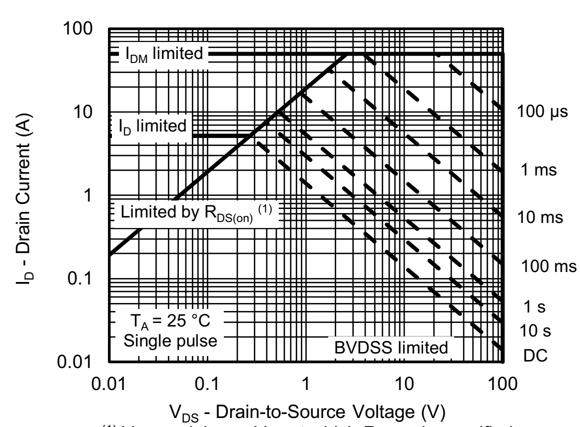
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



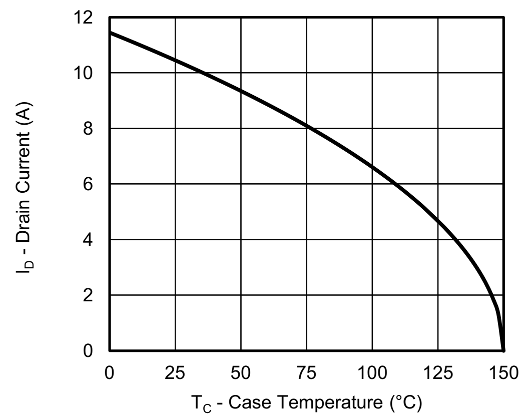
Single Pulse Power, Junction-to-Ambient



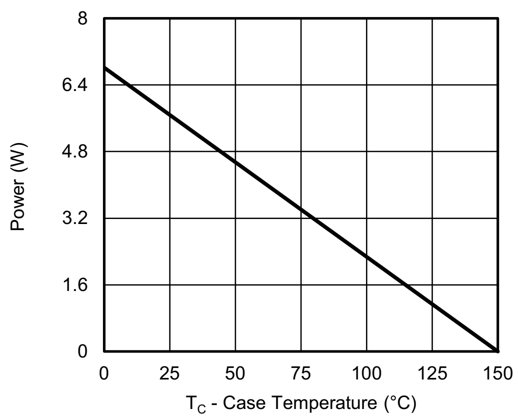
(1) V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

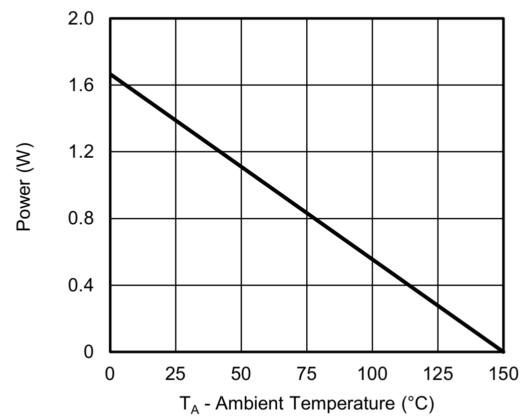
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating [a]



Power, Junction-to-Foot

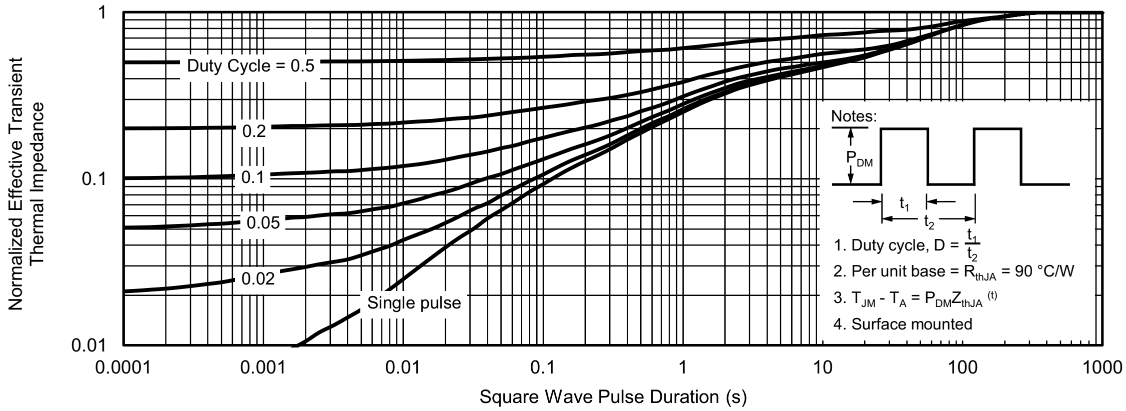


Power, Junction-to-Ambient

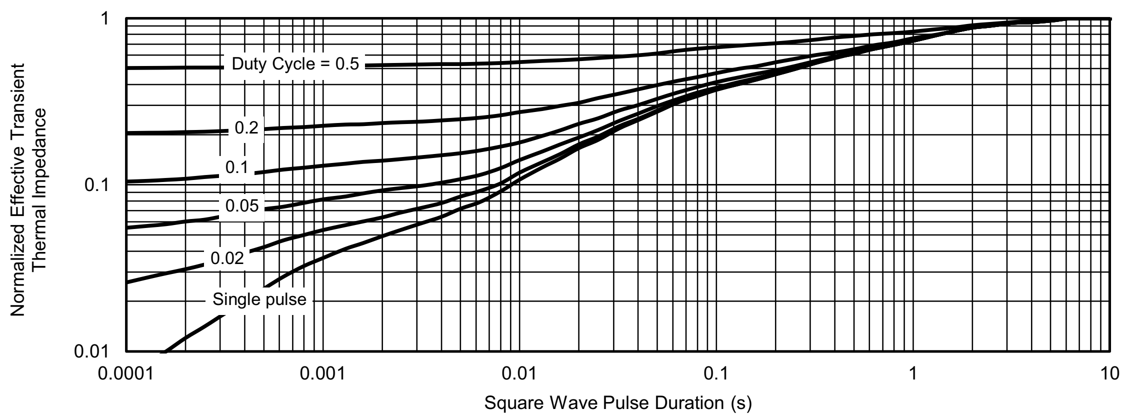
Note

a. The power dissipation P_D is based on T_J (max.) = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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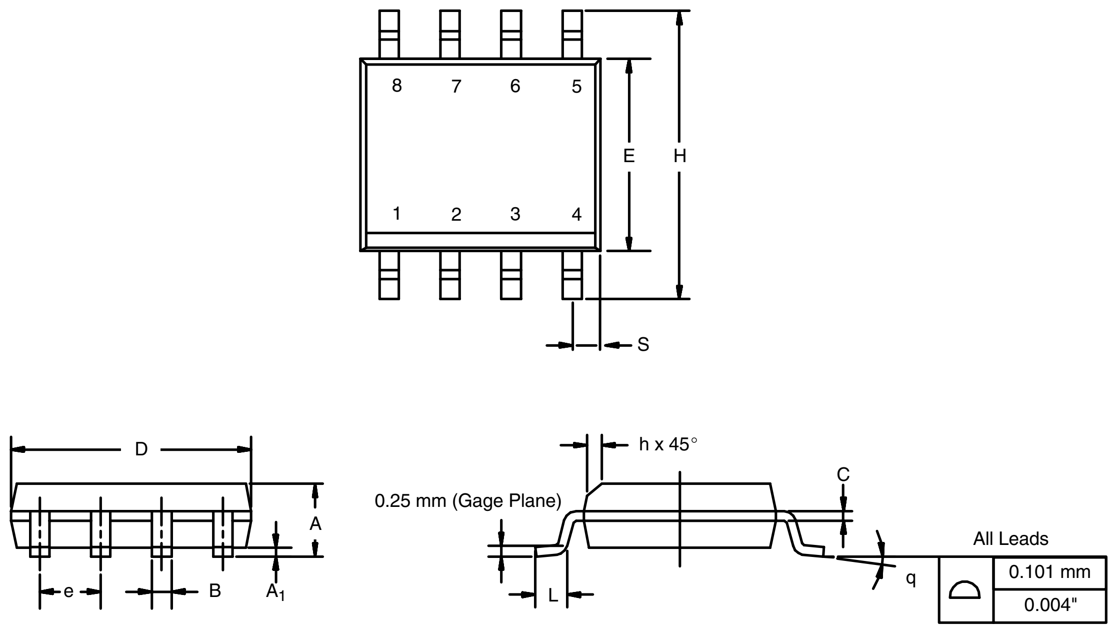
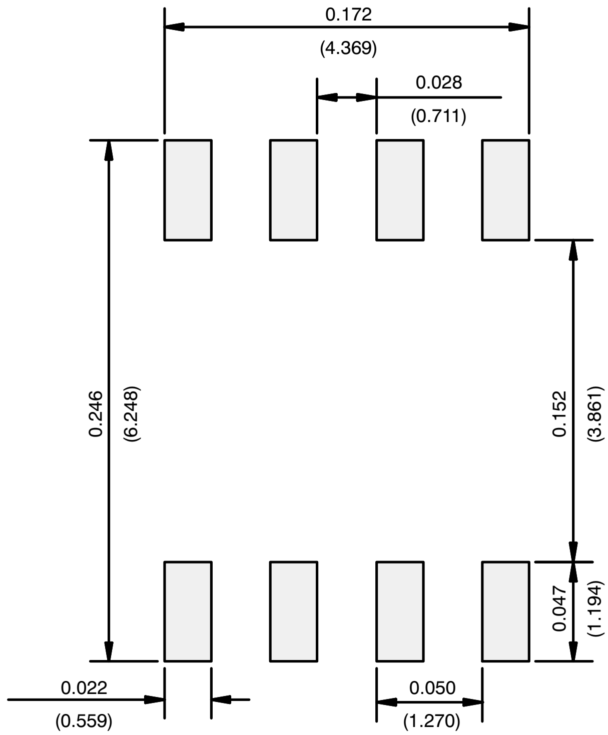
SOIC (NARROW): 8-LEAD
JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A_1	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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